

PUMD24,115 Datasheet





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DiGi Electronics Part Number PUMD24,115-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PUMD24,115

Description TRANS PREBIAS 1NPN 1PNP 6TSSOP

Detailed Description Pre-Biased Bipolar Transistor (BJT) 1 NPN, 1 PNP - P re-Biased (Dual) 50V 20mA 300mW Surface Mount

TEEOD



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PUMD24,115	Nexperia USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
1 NPN, 1 PNP - Pre-Biased (Dual)	20mA
Voltage - Collector Emitter Breakdown (Max):	Resistor - Base (R1):
50V	100kOhms
Resistor - Emitter Base (R2):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100kOhms	80 @ 5mA, 5V
Vce Saturation (Max) @ lb, lc:	Current - Collector Cutoff (Max):
150mV @ 250μA, 5mA	1µА
Frequency - Transition:	Power - Max:
	300mW
Grade:	Qualification:
Automotive	AEC-Q100
Mounting Type:	Package / Case:
Surface Mount	6-TSSOP, SC-88, SOT-363
Supplier Device Package:	Base Product Number:
6-TSSOP	PUMD24

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0095	



PUMD24

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

31 March 2023

Product data sheet

1. General description

NPN/PNP double Resistor-Equipped Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

PNP/PNP complement: PUMB24 NPN/NPN complement: PUMH24

2. Features and benefits

- Built-in bias resistors
- · Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

3. Applications

- Low current peripheral driver
- · Control of IC inputs
- · Replacement of general-purpose transistors in digital applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor	Per transistor							
V _{CEO}	collector-emitter voltage	open base	[1]	-	-	50	V	
I _O	output current		[1]	-	-	20	mA	
R1	bias resistor 1 (input)		[2]	70	100	130	kΩ	
R2/R1	bias resistor ratio	T _{amb} = 25 °C	[2]	0.8	1	1.2		

- [1] For the PNP transistor with negative polarity.
- [2] See section "Test information" for resistor calculation and test conditions.



50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1		
3	O2	output (collector) TR2	6 5 4	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2		TR1 R2 R1
6	01	output (collector) TR1	☐1 ☐2 ☐3	
			TSSOP6 (SOT363)	
				GND1 I1 O2 006aaa143

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PUMD24		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	<u>SOT363</u>		

7. Marking

Table 4. Marking codes

Table 4. Marking codes				
Type number	Marking code[1]			
PUMD24	T8%			

[1] % = placeholder for manufacturing site code

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

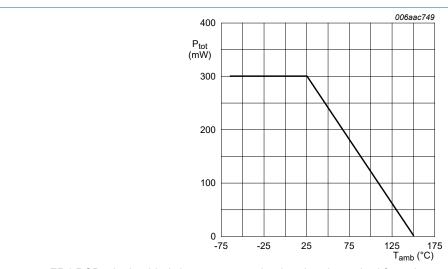
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or		,	1		
V _{CBO}	collector-base voltage	open emitter	[1]	-	50	V
V _{CEO}	collector-emitter voltage	open base	[1]	-	50	V
V_{EBO}	emitter-base voltage	open collector	[1]	-	10	V
V _I	input voltage	input voltage TR1		-10	40	V
		input voltage TR2		-40	10	V
Io	output current		[1]	-	20	mA
I _{CM}	peak collector current		[1]	-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	200	mW
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] For the PNP transistor with negative polarity.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



FR4 PCB, single-sided, 35 μm copper, tin-plated and standard footprint

Fig. 1. Per device: Power derating curve

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	r		'				
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device			'				
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

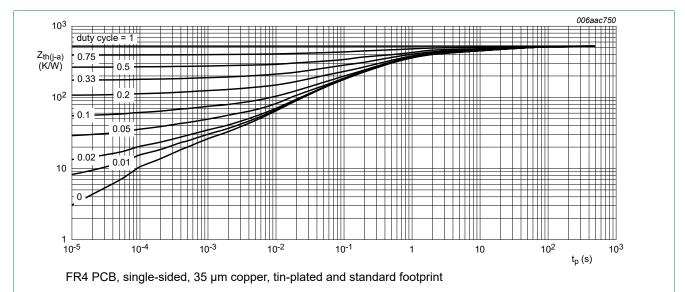


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

10. Characteristics

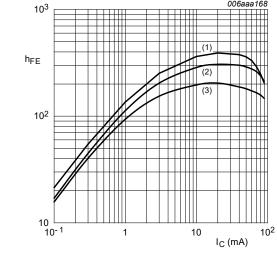
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	or						
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 100 \ \mu\text{A}; \ I_E = 0 \ \text{A}; \ T_{amb} = 25 \ ^{\circ}\text{C}$		50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	[1]	50	-	-	V
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C	[1]	-	-	100	nA
I _{CEO}	collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C	[1]	-	-	100	nA
	current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}; T_{j} = 150 ^{\circ}\text{C}$	[1]	-	-	5	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	[1]	-	-	50	mA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 20 mA; T _{amb} = 25 °C	[1]	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	150	mV
$V_{I(off)}$	off-state input voltage	V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C	[1]	-	1.1	0.5	V
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 1 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	3	1.5	-	V
R1	bias resistor 1 (input)		[2]	70	100	130	kΩ
R2/R1	bias resistor ratio	T _{amb} = 25 °C	[2]	0.8	1	1.2	
TR1 (NPN)							<u>'</u>
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$		-	-	2.5	pF
TR2 (PNP)							
C _c	collector capacitance	V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	3	pF

^[1] For the PNP transistor with negative polarity.

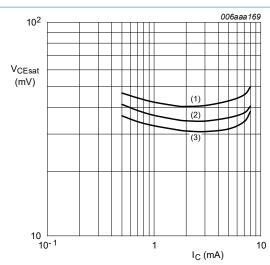
^[2] See section "Test information" for resistor calculation and test conditions.

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 kΩ, R2 = 100 kΩ



V_{CE} = 5 V (1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

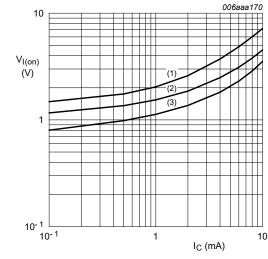
TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values



 $I_{\rm C}/I_{\rm B}=20$

(1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

Fig. 4. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



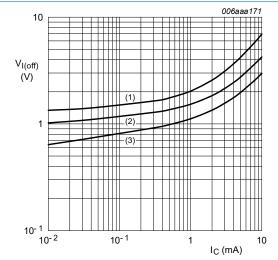
 V_{CE} = 0.3 V

(1) T_{amb} = -40 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 5. TR1 (NPN): On-state input voltage as a function | Fig. 6. of collector current; typical values



 $V_{CE} = 5 V$

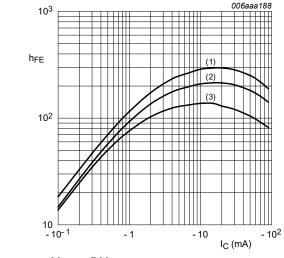
(1) $T_{amb} = -40 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

TR1 (NPN): Off-state input voltage as a function of collector current; typical values

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 kΩ, R2 = 100 kΩ

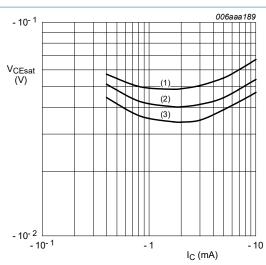


$$V_{CE} = -5 V$$

$$(1) T_{amb} = 100 ° ($$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

TR2 (PNP): DC current gain as a function of Fig. 7. collector current; typical values



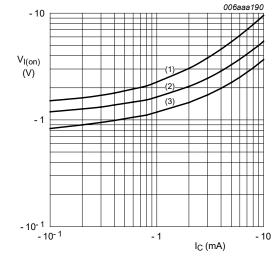
$$I_{\rm C}/I_{\rm B} = 20$$

$$I_{C}/I_{B} = 20$$
(1) $T_{amb} = 100 \, ^{\circ}C$
(2) $T_{amb} = 25 \, ^{\circ}C$
(3) $T_{amb} = -40 \, ^{\circ}C$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 8. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



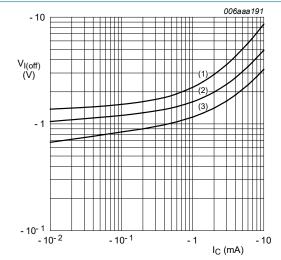
$$V_{CE} = -0.3 \text{ V}$$

$$(1) T_{amb} = -40 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = 100 °C$$

Fig. 9. of collector current; typical values



$$V_{CE}$$
 = -5 V

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

TR2 (PNP): On-state input voltage as a function | Fig. 10. TR2 (PNP): Off-state input voltage as a function of collector current; typical values

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

Resistor calculation

· Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{I})}{I_{2} - I_{I}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

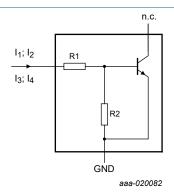


Fig. 11. TR1 (NPN): Resistor test circuit

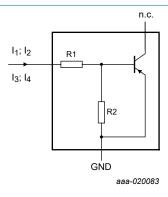


Fig. 12. TR2 (PNP): Resistor test circuit

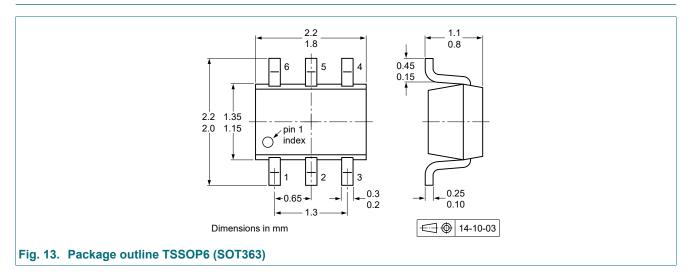
Resistor test conditions

Table 8. Resistor test conditions

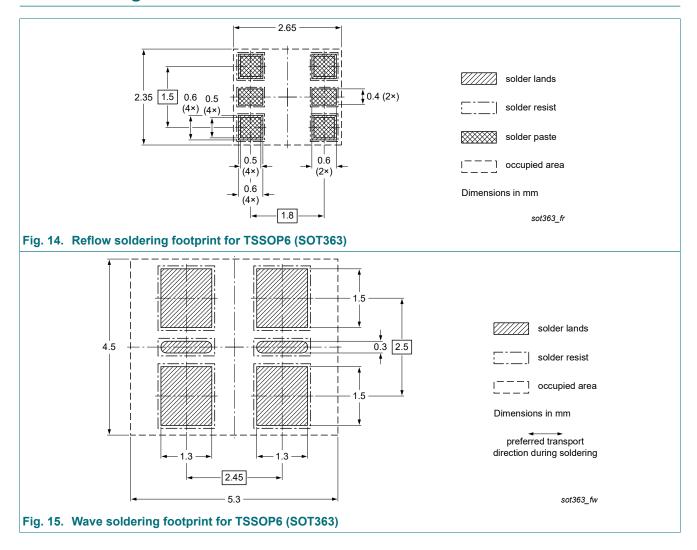
PUMD24	R1 (kΩ)	R2 (kΩ)	Test conditions			
			I ₁	l ₂	l ₃	14
TR1 (NPN)	100	100	20 μΑ	60 μΑ	-20 μA	-40 μA
TR2 (PNP)	100	100	-20 μA	-60 μΑ	20 μΑ	40 µA

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

12. Package outline



13. Soldering



50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PUMD24 v.2	20230331	Product data sheet	-	PEMD24_PUMD24_1
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Family data sheet reduced to single type data sheet. Packing information removed. 			
PEMD24_PUMD24_1	20050502	Product data sheet	-	-

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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PUMD24

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

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